

IRF430, IRF431, IRF432, IRF433

4.0A and 4.5A, 450V and 500V, 1.5 and 2.0 Ohm,
N-Channel Power MOSFETs

November 1997

Features

- 4.0A and 4.5A, 450V and 500V,
- $r_{DS(ON)} = 1.5\Omega$ and 2.0Ω
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Ordering Information

| PART NUMBER | PACKAGE | BRAND |
|-------------|----------|--------|
| IRF430 | TO-204AA | IRF430 |
| IRF431 | TO-204AA | IRF431 |
| IRF432 | TO-204AA | IRF432 |
| IRF433 | TO-204AA | IRF433 |

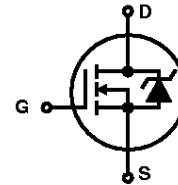
NOTE: When ordering, use the entire part number.

Description

These are N-Channel enhancement mode silicon gate power field effect transistors. They are advanced power MOSFETs designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

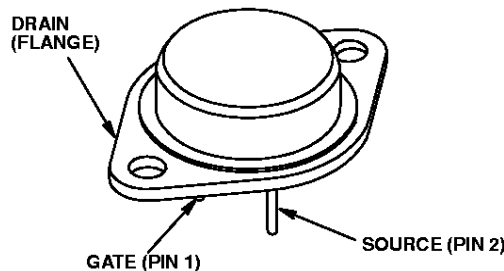
Formerly developmental type TA17415.

Symbol



Packaging

JEDEC TO-204AA



IRF430, IRF431, IRF432, IRF433

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

| | IRF430 | IRF431 | IRF432 | IRF433 | UNITS |
|---|------------|------------|------------|------------|---------------------|
| Drain to Source Breakdown Voltage (Note 1) V_{DS} | 500 | 450 | 500 | 450 | V |
| Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1) V_{DGR} | 500 | 450 | 500 | 450 | V |
| Continuous Drain Current I_D | 4.5 | 4.5 | 4.0 | 4.0 | A |
| $T_C = 100^\circ\text{C}$ I_D | 3.0 | 3.0 | 2.5 | 2.5 | A |
| Pulsed Drain Current (Note 3) I_{DM} | 18 | 18 | 16 | 16 | A |
| Gate to Source Voltage V_{GS} | ± 20 | ± 20 | ± 20 | ± 20 | V |
| Maximum Power Dissipation P_D | 75 | 75 | 75 | 75 | W |
| Dissipation Derating Factor | 0.6 | 0.6 | 0.6 | 0.6 | W/ $^\circ\text{C}$ |
| Single Pulse Avalanche Energy Rating (Note 4) E_{AS} | 300 | 300 | 300 | 300 | mJ |
| Operating and Storage Temperature T_J, T_{STG} | -55 to 150 | -55 to 150 | -55 to 150 | -55 to 150 | $^\circ\text{C}$ |
| Maximum Temperature for Soldering | | | | | |
| Leads at 0.063in (1.6mm) from Case for 10s T_L | 300 | 300 | 300 | 300 | $^\circ\text{C}$ |
| Package Body for 10s, See Techbrief 334 T_{pkg} | 260 | 260 | 260 | 260 | $^\circ\text{C}$ |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

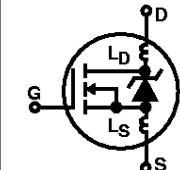
- $T_J = 25^\circ\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

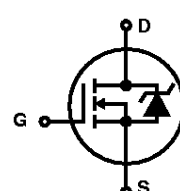
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|--|--------------|--|----------------|-----|-----------|---------------|
| Drain to Source Breakdown Voltage IRF430, IRF432 | BV_{DSS} | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ (Figure 10) | 500 | - | - | V |
| | | | IRF431, IRF433 | 450 | - | - |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ | 2.0 | - | 4.0 | V |
| Gate to Source Leakage Current | I_{GSS} | $V_{GS} = \pm 20\text{V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = \text{Rated } BV_{DSS}, V_{GS} = 0\text{V}$ | - | - | 25 | μA |
| | | $V_{DS} = 0.8 \times \text{Rated } BV_{DSS}, V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$ | - | - | 250 | μA |
| On-State Drain Current (Note 2) IRF430, IRF431 | $I_{D(ON)}$ | $V_{DS} > I_{D(ON)} \times r_{DS(ON)MAX}, V_{GS} = 10\text{V}$ (Figure 7) | 4.5 | - | - | A |
| | | | IRF432, IRF433 | 4.0 | - | - |
| Drain to Source On Resistance (Note 2) IRF430, IRF431 | $r_{DS(ON)}$ | $I_D = 2.5\text{A}, V_{GS} = 10\text{V}$ (Figures 8, 9) | - | 1.3 | 1.5 | Ω |
| | | | IRF432, IRF433 | - | 1.5 | 2.0 |
| Forward Transconductance (Note 2) | g_{fs} | $V_{DS} \geq 50\text{V}, I_D = 2.5\text{A}$ (Figure 12) | 2.7 | 3.2 | - | S |
| Turn-On Delay Time | $t_{d(ON)}$ | $V_{DD} = 250\text{V}, I_D \approx 4.5\text{A}, R_G = 12\Omega, R_L = 50\Omega,$ (Figures 17, 18) MOSFET Switching Times are Essentially Independent of Operating Temperature | - | 11 | 17 | ns |
| Rise Time | t_r | | - | 15 | 23 | ns |
| Turn-Off Delay Time | $t_{d(OFF)}$ | | - | 35 | 53 | ns |
| Fall Time | t_f | | - | 15 | 23 | ns |
| Total Gate Charge (Gate to Source + Gate to Drain) | $Q_{g(TOT)}$ | $V_{GS} = 10\text{V}, I_D \approx 6.0\text{A}, V_{DS} = 0.8 \times \text{Rated } BV_{DSS}, I_{g(REF)} = 1.5\text{mA}$ (Figures 14, 19, 20) Gate Charge is Essentially Independent of Operating Temperature | - | 22 | 32 | nC |
| Gate to Source Charge | Q_{gs} | | - | 3.5 | - | nC |
| Gate to Drain "Miller" Charge | Q_{gd} | | - | 11 | - | nC |

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Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified (Continued)

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN | TYP | MAX | UNITS |
|--|-----------------|---|---|-----|------|------|--------------------|
| Input Capacitance | C_{ISS} | $V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ (Figure 11) | | - | 600 | - | pF |
| Output Capacitance | C_{OSS} | | | - | 100 | - | pF |
| Reverse Transfer Capacitance | C_{RSS} | | | - | 30 | - | pF |
| Internal Drain Inductance | L_D | Measured Between the Contact Screw on the Flange that is Closer to Source and Gate Pins and the Center of Die | Modified MOSFET Symbol Showing the Internal Devices Inductances  | - | 5.0 | - | nH |
| Internal Source Inductance | L_S | Measured From The Source Lead, 6mm (0.25in) From the Flange and the Source Bonding Pad | | - | 12.5 | - | nH |
| Thermal Resistance Junction to Case | $R_{\theta JC}$ | | | - | - | 0.83 | $^\circ\text{C/W}$ |
| Thermal Resistance Junction to Ambient | $R_{\theta JA}$ | Free Air Operation | | - | - | 30 | $^\circ\text{C/W}$ |

Source to Drain Diode Specifications

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN | TYP | MAX | UNITS |
|--|-----------|---|---|------|-----|-----|---------------|
| Continuous Source to Drain Current | I_{SD} | Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Diode  | - | - | 4.5 | A | |
| Pulse Source to Drain Current (Note 3) | I_{SDM} | | - | - | 18 | A | |
| Source to Drain Diode Voltage (Note 2) | V_{SD} | $T_J = 25^\circ\text{C}$, $I_{SD} = 4.5\text{A}$, $V_{GS} = 0\text{V}$ (Figure 13) | | - | - | 1.4 | V |
| Reverse Recovery Time | t_{rr} | $T_J = 25^\circ\text{C}$, $I_{SD} = 4.5\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$ | | 180 | 370 | 760 | ns |
| Reverse Recovery Charge | Q_{RR} | $T_J = 25^\circ\text{C}$, $I_{SD} = 4.5\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$ | | 0.96 | 2 | 4.3 | μC |

NOTES:

2. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Repetitive rating: pulse width limited by max junction temperature. See Transient Thermal Impedance curve (Figure 3).
4. $V_{DD} = 50\text{V}$, starting $T_J = 25^\circ\text{C}$, $L = 25\text{mH}$, $R_G = 25\Omega$, peak $I_{AS} = 4.5\text{A}$. See Figures 15, 16.

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Typical Performance Curves Unless Otherwise Specified

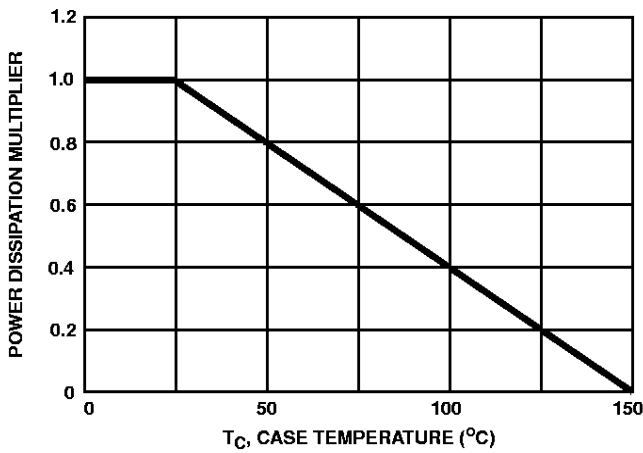


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

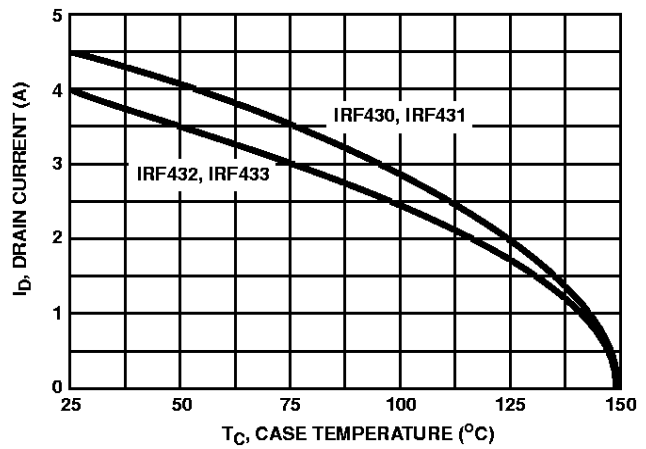


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

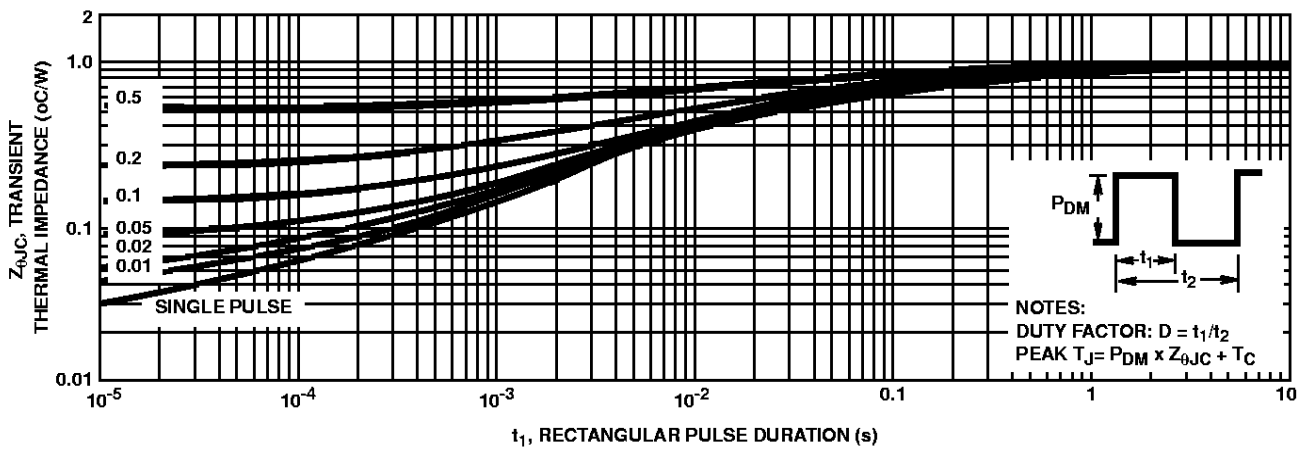


FIGURE 3. MAXIMUM TRANSIENT THERMAL IMPEDANCE

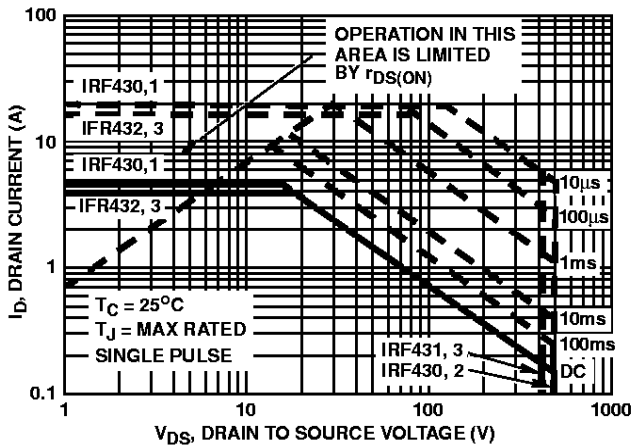


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

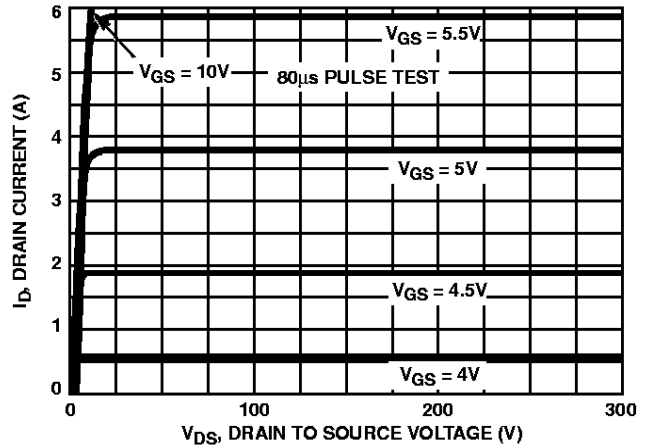


FIGURE 5. OUTPUT CHARACTERISTICS

Typical Performance Curves Unless Otherwise Specified (Continued)

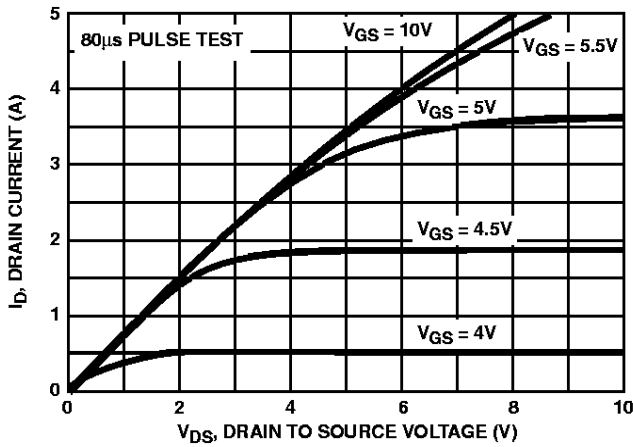


FIGURE 6. SATURATION CHARACTERISTICS

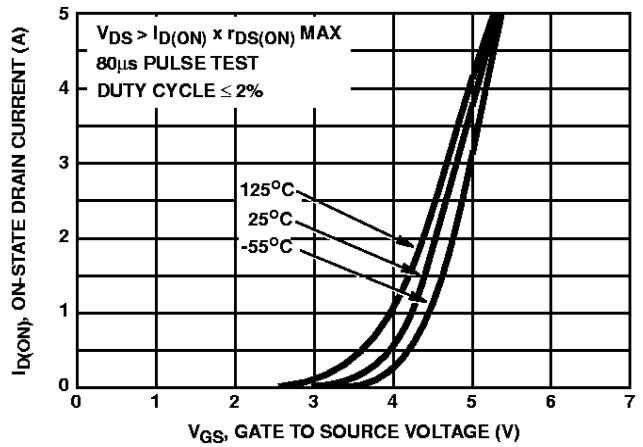
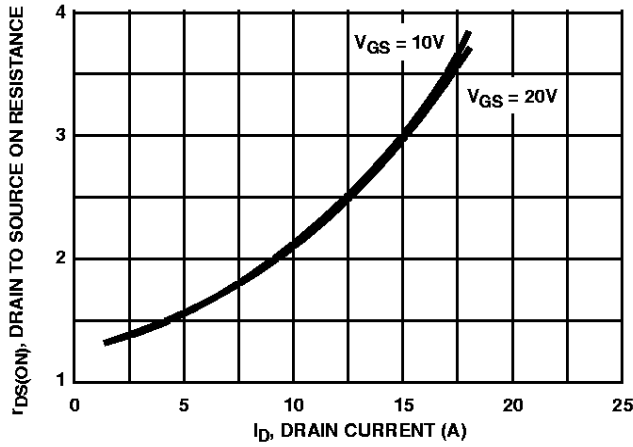


FIGURE 7. TRANSFER CHARACTERISTICS



NOTE: Heating effect of 2µs pulse is minimal.

FIGURE 8. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

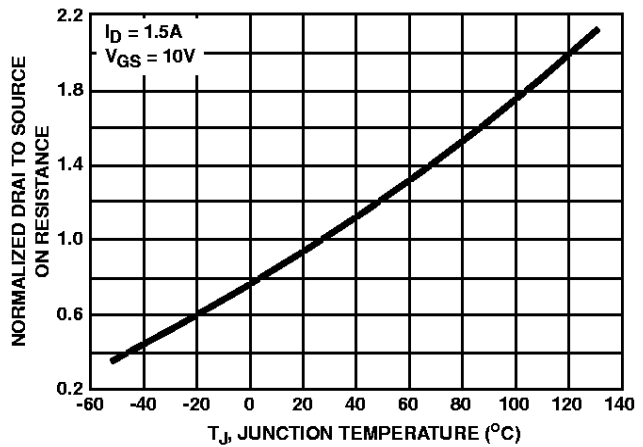


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

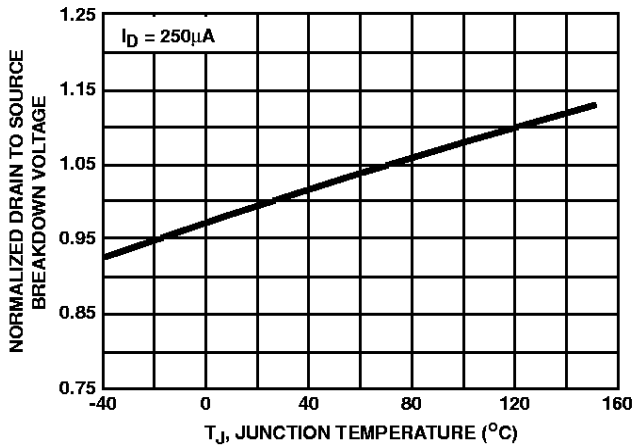


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

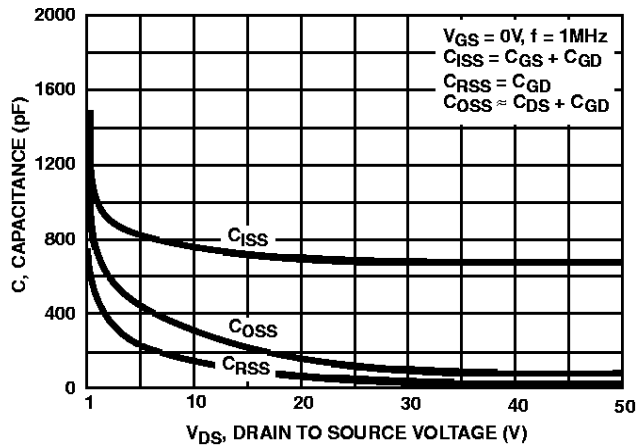


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

Typical Performance Curves Unless Otherwise Specified (Continued)

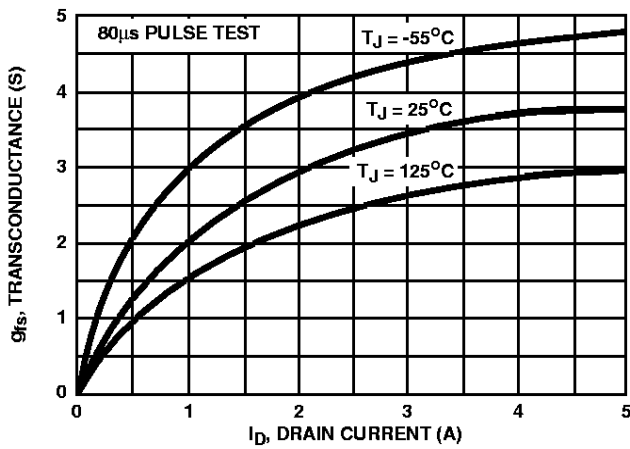


FIGURE 12. TRANSCONDUCTANCE vs DRAIN CURRENT

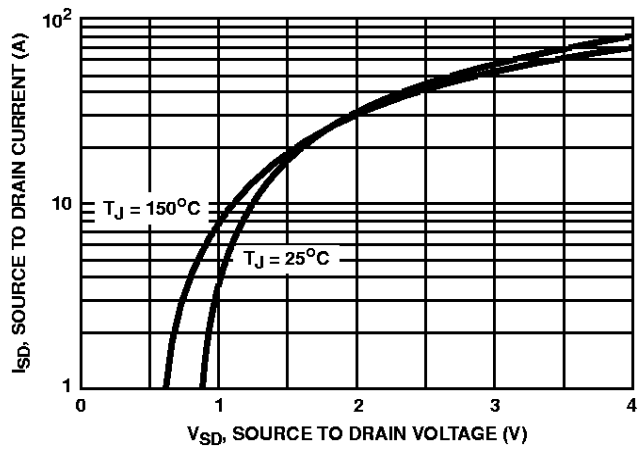


FIGURE 13. SOURCE TO DRAIN DIODE VOLTAGE

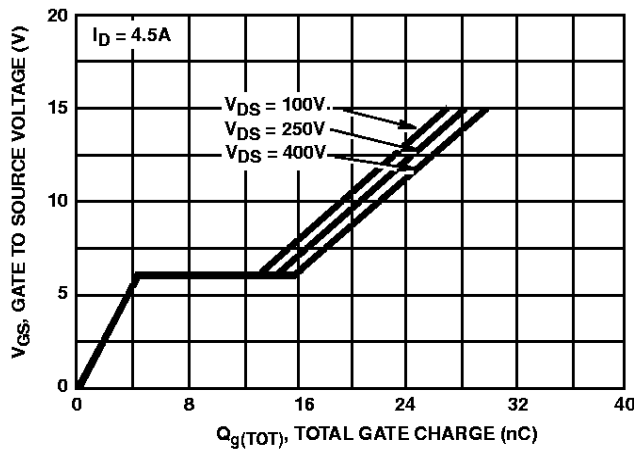


FIGURE 14. GATE TO SOURCE VOLTAGE vs GATE CHARGE

Test Circuits and Waveforms

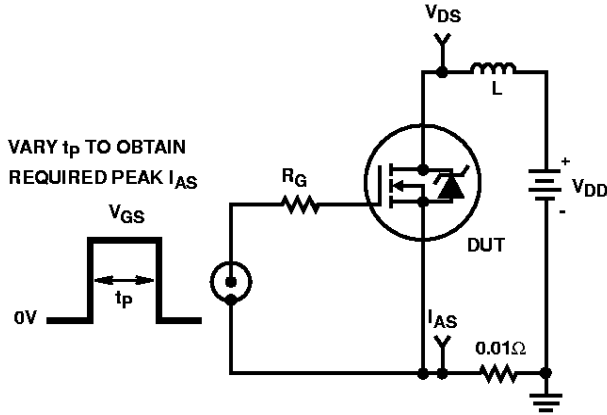


FIGURE 15. UNCLAMPED ENERGY TEST CIRCUIT

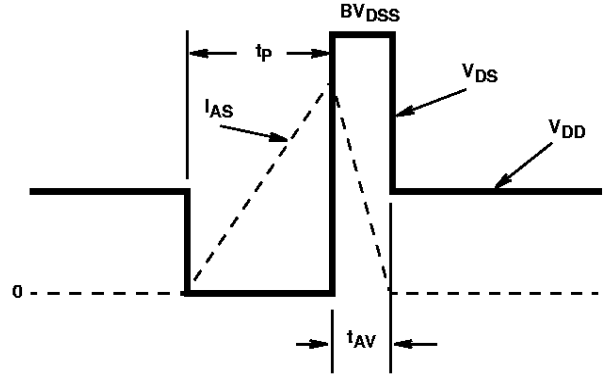


FIGURE 16. UNCLAMPED ENERGY WAVEFORMS

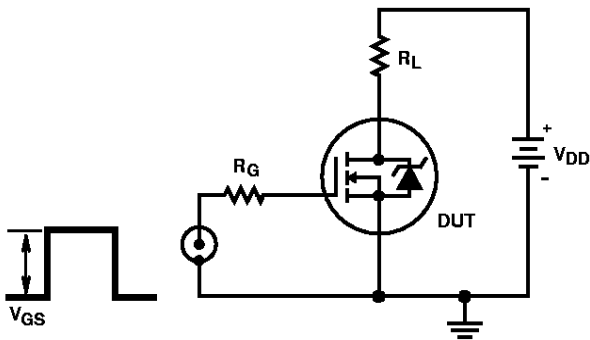


FIGURE 17. SWITCHING TIME TEST CIRCUIT

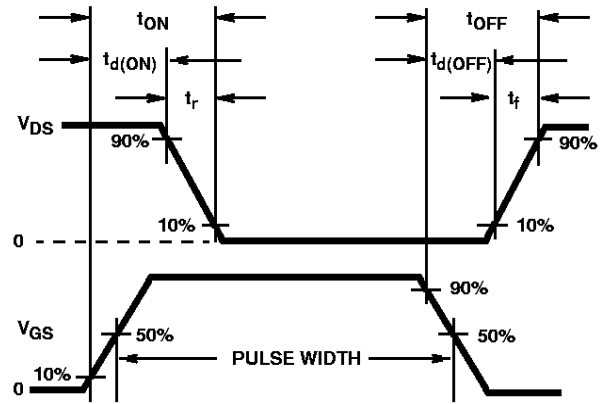


FIGURE 18. RESISTIVE SWITCHING WAVEFORMS

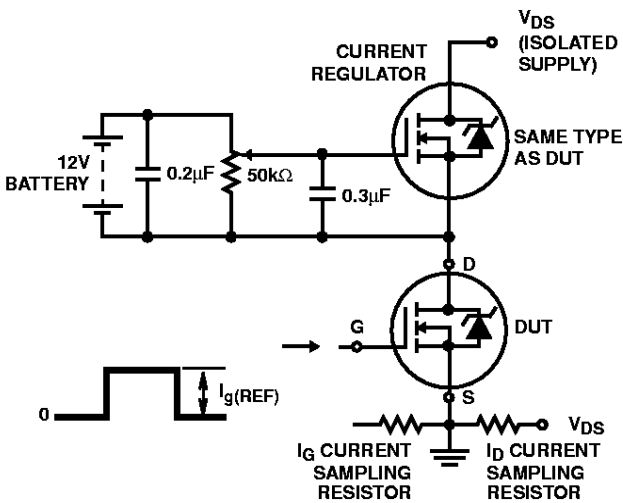


FIGURE 19. GATE CHARGE TEST CIRCUIT

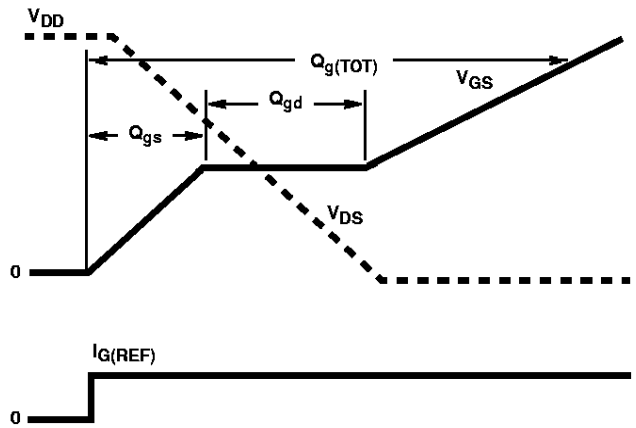


FIGURE 20. GATE CHARGE WAVEFORMS